

BSR31 BSR33

SMALL SIGNAL PNP TRANSISTORS

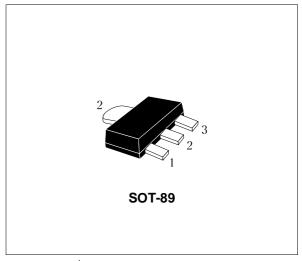
PRELIMINARY DATA

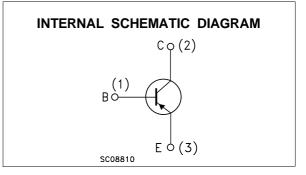
Ordering Code	Marking
BSR31	R31
BSR33	R33

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTORS
- SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPES ARE BSR41 AND BSR43 RESPECTIVELY

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Va	Unit	
		BSR31	BSR33	
V _{CBO}	Collector-Base Voltage (I _E = 0)	-70	-90	V
Vceo	Collector-Emitter Voltage (I _B = 0)	-60	-80	V
Vево	Emitter-Base Voltage (Ic = 0)	-5		V
Ic	Collector Current	-1		Α
Ісм	Collector Peak Current (tp < 5 ms)	-2		Α
IB	Base Current	-0.1		Α
I _{BM}	Base Peak Current (t _p < 5 ms)	-0.2		Α
P _{tot}	Total Dissipation at T _{amb} = 25 °C	1.35		W
T _{stg}	Storage Temperature	-65 to 150		°C
Tj	Max. Operating Junction Temperature	150		°C

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	92.6	°C/W
 Device mour 	ted on a PCB area of 1 cm ²			

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

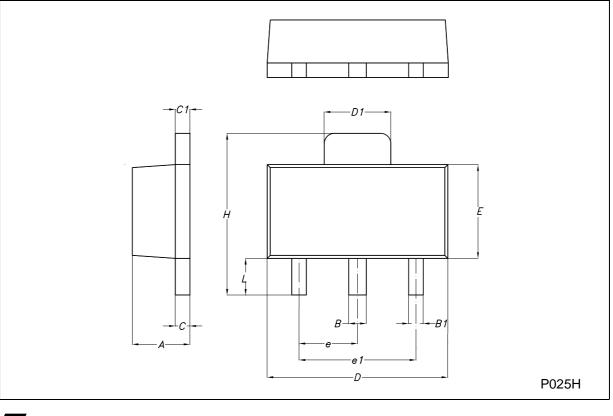
Symbol	Symbol Parameter		Test Conditions		Тур.	Max.	Unit
I _{СВО}	Collector Cut-off Current ($I_E = 0$)	V _{CB} = -60 V V _{CB} = -60 V	T _j = 150 °C			-100 -50	nΑ μΑ
I _{EBO}	Emitter Cut-off Current $(I_c = 0)$	V _{EB} = -5 V				-100	nA
V _(BR) CBO	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA for BSR31 for BSR33		-70 -90			V V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA for BSR31 for BSR33		-60 -80			V V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA		-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{C} = -150 \text{ mA}$ I $I_{C} = -500 \text{ mA}$ I				-0.25 -0.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = -150 mA I I _C = -500 mA I	в = -15 mA в = -50 mA			-1 -1.2	V V
h _{FE} *	DC Current Gain	$I_{C} = -100 \ \mu A$ $I_{C} = -100 \ m A$ $I_{C} = -500 \ m A$		30 100 50		300	
f _T	Transition Frequency	f = 100 MHz	V _{CE} = -10 V	100			MHz

57

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle \leq 1.5 %

DIM.	mm			mils		
2.111	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	1.4		1.6	55.1		63.0
В	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
С	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
Е	2.29		2.6	90.2		102.4
е	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
Н	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2







Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

47/

4/4